

MMBT3906T PNP Epitaxial Silicon Transistor

Features

- General purpose amplifier transistor.
- Ultra-Small Surface Mount Package for all types.
- Suitable for general switching & amplification
- · Well suited for portable application
- As complementary type, NPN MMBT3904T is recommended



February 2008

Absolute Maximum Ratings T_a = 25°C unless otherwise noted

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
l _C	Collector Current	200	mA
Т _Ј	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 ~ 150	°C

These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics* Ta=25°C unless otherwise noted

Symbol	Parameter	Max	Unit
P _C	Collector Power Dissipation, by $R_{\theta JA}$	250	mW
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	500	°C/W

* Minimum land pad.

Electrical Characteristics* T_=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = -10\mu A, I_{E} = 0$	-40		V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = -1 {\rm mA}, I_{\rm B} = 0$	40		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{E} = -10\mu A, I_{C} = 0$	-5		V
I _{CEX}	Collector Cut-off Current	$V_{CE} = -30V, V_{EB(OFF)} = -0.3V$		-50	nA
h _{FE}	DC Current Gain	$V_{CE} = 1V, I_{C} = -0.1mA$ $V_{CE} = 1V, I_{C} = -1mA$ $V_{CE} = 1V, I_{C} = -10mA$ $V_{CE} = 1V, I_{C} = -10mA$ $V_{CE} = 1V, I_{C} = -50mA$ $V_{CE} = 1V, I_{C} = -100mA$	60 80 100 60 30	300	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_{C} = -10$ mA, $I_{B} = -1$ mA $I_{C} = -50$ mA, $I_{B} = -5$ mA		-0.25 -0.4	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = -10mA, I _B = -1mA I _C = -50mA, I _B = -5mA	-0.65	-0.85 -0.95	V V
f _T	Current Gain Bandwidth Product	$V_{CE} = -20V, I_{C} = -10mA, f = 100MHz$	250		MHz
C _{ob}	Output Capacitance	$V_{CB} = -5V, I_E = 0, f = 1MHz$		7.0	pF
C _{ib}	Input Capacitance	$V_{EB} = -0.5V, I_{C} = 0, f = 1MHz$		15	pF
t _d	Delay Time	$V_{CC} = -3V, I_{C} = -10mA$		35	ns
t _r	Rise Time	I _{B1} =- I _{B2} = -1mA		35	ns
t _s	Storage Time			225	ns
t _f	Fall Time			75	ns

DC Item are tested by Pulse Test : Pulse Width≤300us, Duty Cycle≤2%

Typical Performance Characteristics

Figure 1. DC Current Gain

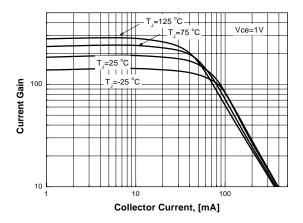
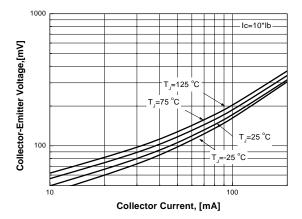
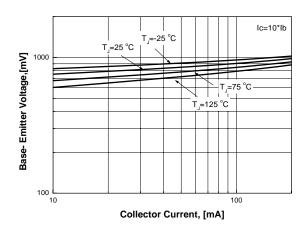


Figure 2. Collector-Emitter Saturation Voltage









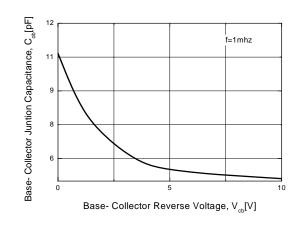
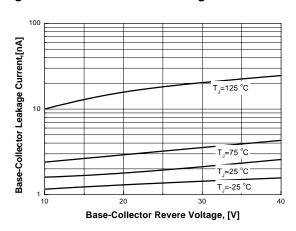
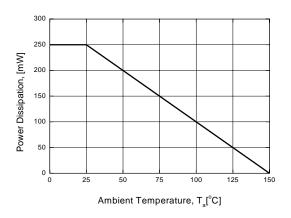
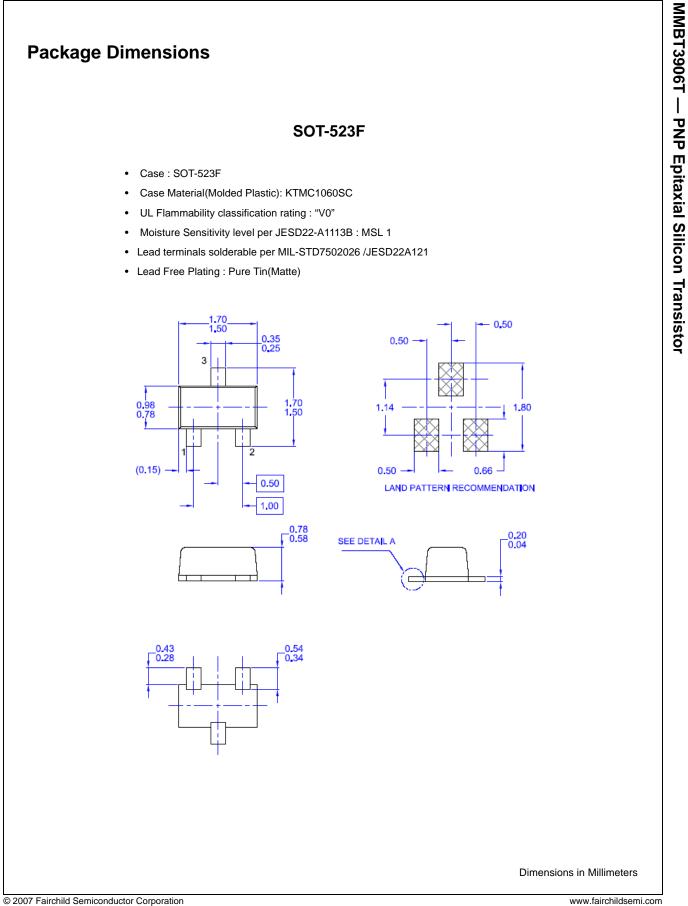


Figure 4. Collector- Base Leakage Current









MMBT3906T Rev. 1.0.0



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